

Thyristor \ Diode Module

V_{RRM} = 2x 1600 V

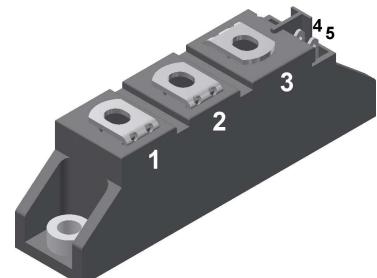
I_{TAV} = 25 A

V_T = 1.2 V

Phase leg

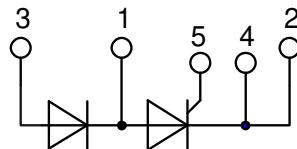
Part number

MCMA25PD1600TB



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

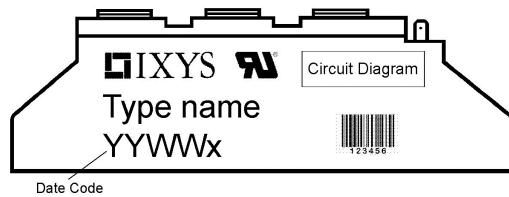
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Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1600	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1600 V$ $V_{R/D} = 1600 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 140^\circ C$		100 4	μA mA
V_T	forward voltage drop	$I_T = 25 A$	$T_{VJ} = 25^\circ C$		1.22	V
		$I_T = 50 A$			1.47	V
		$I_T = 25 A$	$T_{VJ} = 125^\circ C$		1.20	V
		$I_T = 50 A$			1.52	V
I_{TAV}	average forward current	$T_C = 85^\circ C$	$T_{VJ} = 140^\circ C$		25	A
$I_{T(RMS)}$	RMS forward current	180° sine			40	A
V_{T0}	threshold voltage	r_T slope resistance } for power loss calculation only	$T_{VJ} = 140^\circ C$		0.87	V
	slope resistance				13	$m\Omega$
R_{thJC}	thermal resistance junction to case				1.2	K/W
R_{thCH}	thermal resistance case to heatsink			0.2		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		90	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		400	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		430	A
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 140^\circ C$		340	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		365	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		800	A^2s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		770	A^2s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 140^\circ C$		580	A^2s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 V$		555	A^2s
C_J	junction capacitance	$V_R = 400 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	16		pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 140^\circ C$		10	W
		$t_p = 300 \mu s$			5	W
P_{GAV}	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^\circ C; f = 50 \text{ Hz}$	repetitive, $I_T = 75 A$		150	$A/\mu s$
		$t_p = 200 \mu s; di_G/dt = 0.45 A/\mu s;$				
		$I_G = 0.45 A; V = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 25 A$		500	$A/\mu s$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ C$		1000	$V/\mu s$
		$R_{GK} = \infty$; method 1 (linear voltage rise)				
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^\circ C$		1.5	V
			$T_{VJ} = -40^\circ C$		1.6	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^\circ C$		55	mA
			$T_{VJ} = -40^\circ C$		80	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^\circ C$		0.2	V
I_{GD}	gate non-trigger current				5	mA
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^\circ C$		150	mA
		$I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$				
I_H	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ C$		100	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^\circ C$		2	μs
		$I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = 25 A; V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ C$	150		μs
		$di/dt = 10 A/\mu s$ $dv/dt = 20 V/\mu s$ $t_p = 200 \mu s$				

Package TO-240AA			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			60	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				81		g
M_D	mounting torque		2.5		4	Nm
M_T	terminal torque		2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	13.0	9.7		mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4800 4000		V V



Part description

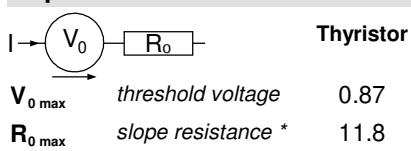
M = Module
 C = Thyristor (SCR)
 M = Thyristor
 A = (up to 1800V)
 25 = Current Rating [A]
 PD = Phase leg
 1600 = Reverse Voltage [V]
 TB = TO-240AA-1B

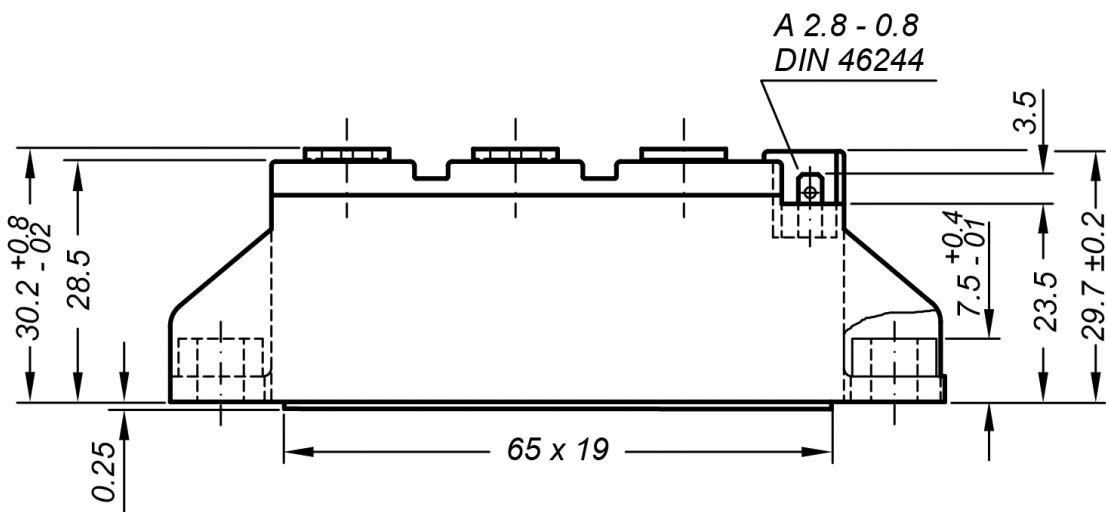
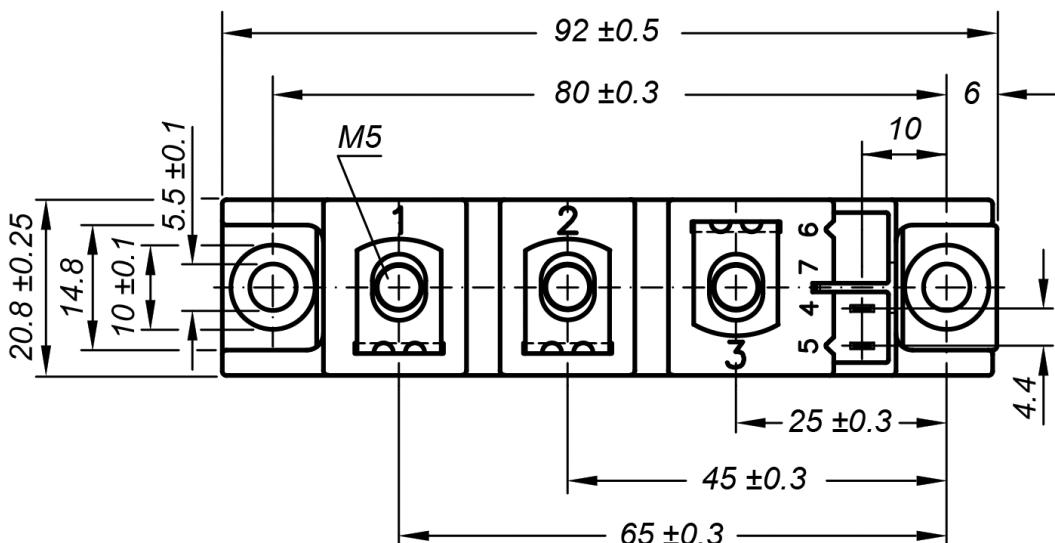
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA25PD1600TB	MCMA25PD1600TB	Box	36	515042

Equivalent Circuits for Simulation

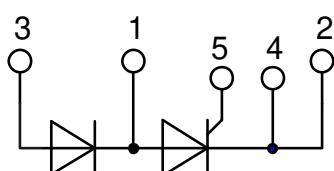
* on die level

$T_{VJ} = 140^\circ\text{C}$



Outlines TO-240AA

General tolerance: DIN ISO 2768 class „c“

Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
Type ZY 200L (L = Left for pin pair 4/5) UL 758, style 3751



Thyristor

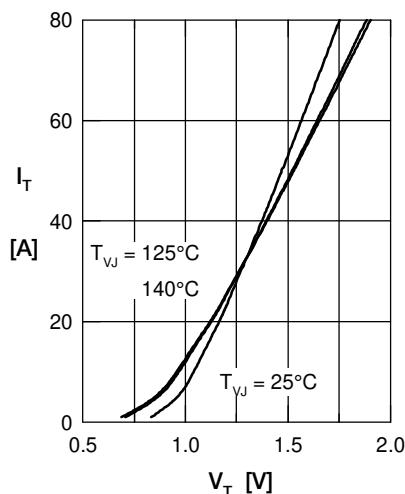


Fig. 1 Forward characteristics

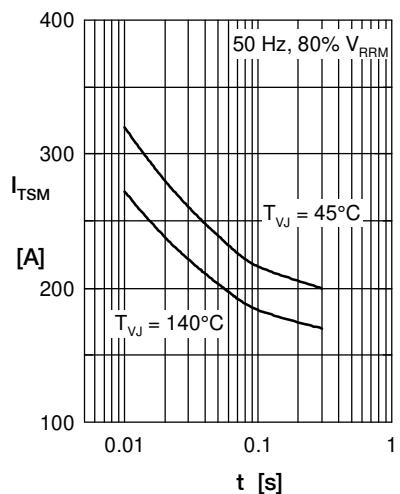


Fig. 2 Surge overload current
 I_{TSM} : crest value, t : duration

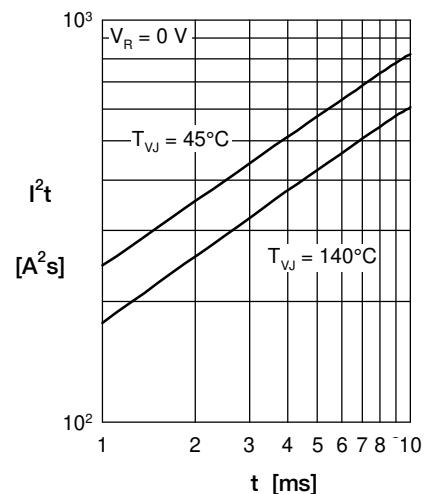


Fig. 3 I^2t versus time (1-10 s)

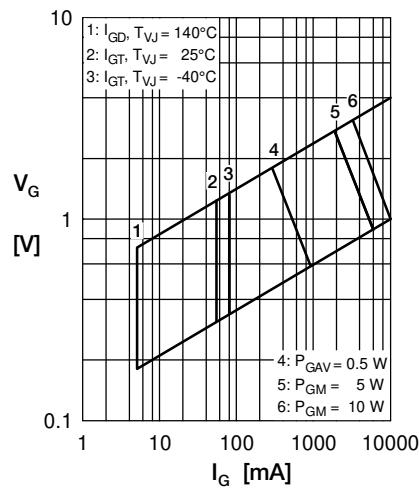


Fig. 4 Gate voltage & gate current

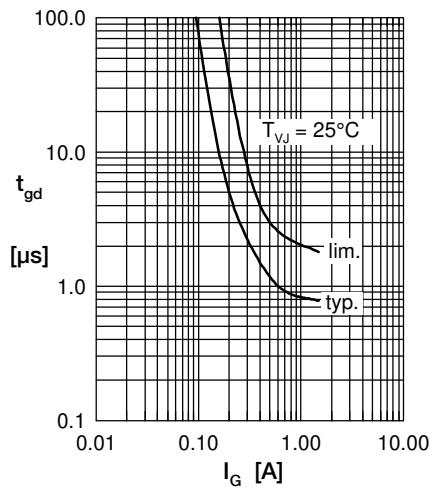


Fig. 5 Gate controlled delay time t_{gd}

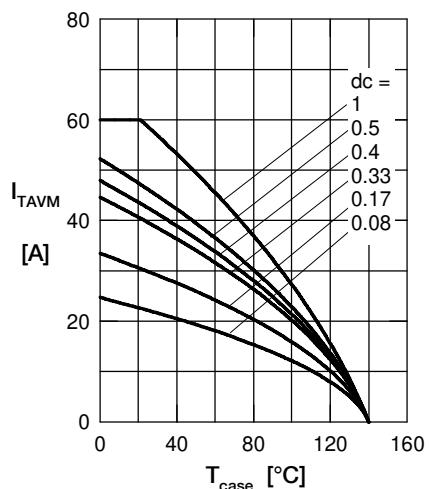


Fig. 6 Max. forward current at case temperature

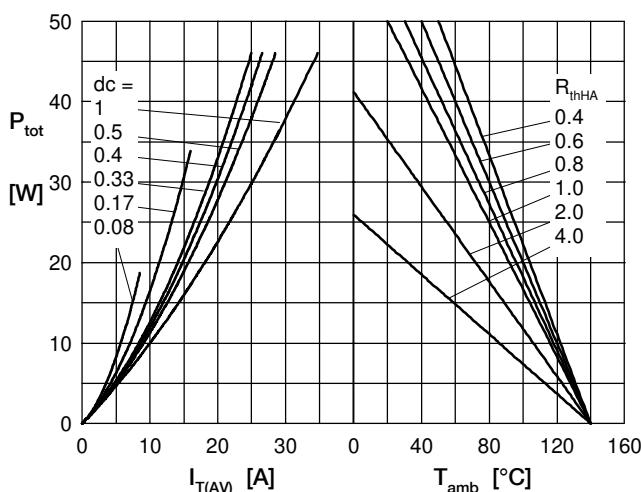


Fig. 7a Power dissipation versus direct output current
Fig. 7b and ambient temperature

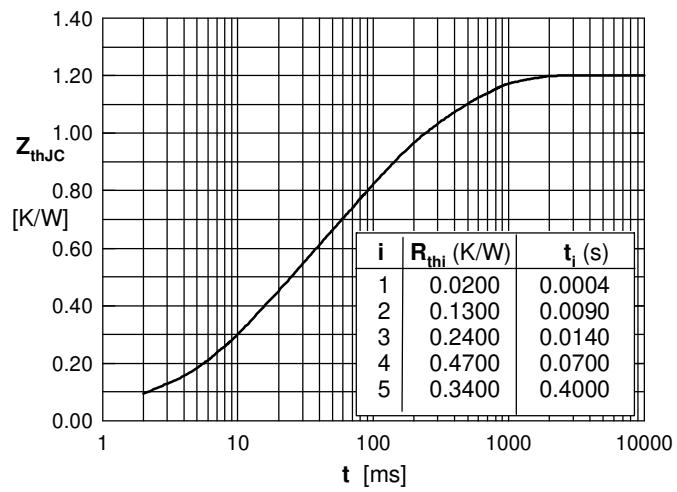


Fig. 8 Transient thermal impedance junction to case